5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	Α	anode		K — A 001aaa020
mb	n.c.	mounting base; isolated		001aaa020

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BYC5X-600P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220F "full pack"	SOD113A			

7. Marking

Table 4. Marking codes

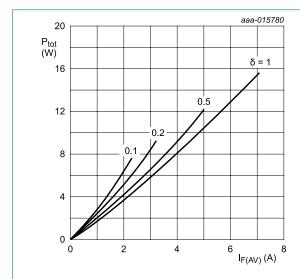
Type number	Marking codes
BYC5X-600P	BYC5X-600P

8. Limiting values

Table 5. Limiting values

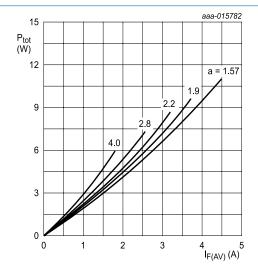
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	$δ = 0.5$; square-wave pulse; $T_h \le 97$ °C; Fig. 1; Fig. 2; Fig. 3	5	А
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_h \le 97 °C$; square-wave pulse	10	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	60	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	65	А
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C



$$\begin{split} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{o}} &= 1.801 \text{ V; } R_{\text{s}} = 0.062 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 1.801 V; R_s = 0.062 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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Hyperfast power diode

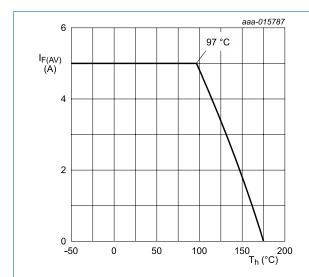


Fig. 3. Forward current as a function of heatsink temperature; maximum values

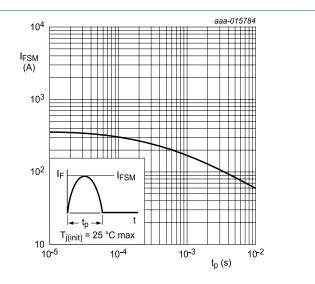


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; Fig 5	-	-	6.5	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W

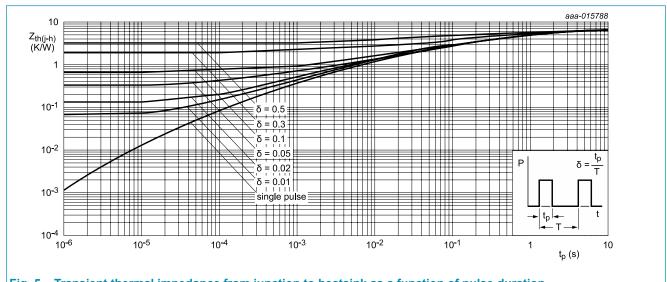


Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

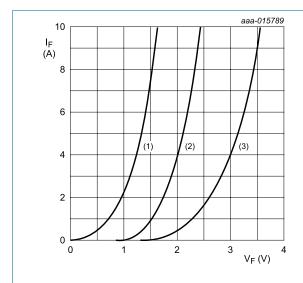
Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all pins to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink; f = 1 MHz	-	10	-	pF

11. Characteristics

Table 8 Characteristics

Danasatan						
Parameter	Conditions		Viin	Тур	Max	Unit
aracteristics						
forward voltage	I _F = 5 A; T _j = 25 °C; <u>Fig. 6</u>	-	-	2.5	3.3	V
	I _F = 5 A; T _j = 150 °C; <u>Fig. 6</u>	-	-	1.35	2.1	V
reverse current	V _R = 600 V; T _j = 25 °C	-		-	10	μA
	V _R = 600 V; T _j = 150 °C	-	-	-	0.6	mA
characteristics						
recovered charge	$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	19	-	nC
	$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	-	45	-	nC
reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	11	-	ns
	$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	23	-	ns
	$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	-	28	-	ns
	$I_F = 5 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	13	25	ns
peak reverse recovery current	$I_F = 5 \text{ A}$; $V_R = 200 \text{ V}$; $dI_F/dt = 200 \text{ A}/\mu\text{s}$; $T_J = 25 ^{\circ}\text{C}$; Fig. 7	-	-	1.7	-	А
	$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_i = 125 \text{ °C}; Fig. 7$	-	-	3.2	-	А
	reverse current characteristics recovered charge reverse recovery time	$ I_F = 5 \text{ A}; T_j = 25 \text{ °C}; \underline{\text{Fig. 6}} \\ I_F = 5 \text{ A}; T_j = 150 \text{ °C}; \underline{\text{Fig. 6}} \\ I_F = 5 \text{ A}; T_j = 150 \text{ °C}; \underline{\text{Fig. 6}} \\ I_F = 5 \text{ A}; T_j = 150 \text{ °C} \\ V_R = 600 \text{ V}; T_j = 25 \text{ °C} \\ V_R = 600 \text{ V}; T_j = 150 \text{ °C} \\ V_R = 600 \text{ V}; T_j = 150 \text{ °C} \\ V_R = 600 \text{ V}; T_j = 150 \text{ °C} \\ V_R = 200 \text{ V}; V_R = 200 \text{ V}; V_R = 200 \text{ A/μ}; \\ T_j = 25 \text{ °C}; \underline{\text{Fig. 7}} \\ I_F = 5 \text{ A}; V_R = 200 \text{ V}; V_R = 200 \text{ A/μ}; \\ T_j = 125 \text{ °C}; \underline{\text{Fig. 7}} \\ I_F = 1 \text{ A}; V_R = 30 \text{ V}; V_R = 200 \text{ A/μ}; \\ T_j = 25 \text{ °C}; \underline{\text{Fig. 7}} \\ I_F = 5 \text{ A}; V_R = 200 \text{ V}; V_R = 200 \text{ A/μ}; \\ T_j = 125 \text{ °C}; \underline{\text{Fig. 7}} \\ I_F = 5 \text{ A}; V_R = 400 \text{ V}; 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} V_{_{R}} = 200 \text{ V; } dI_{_{F}}/dt = 200 \text{ A/}\mu\text{s; } \\ T_{_{J}} = 25 \text{ °C; } \underline{\text{Fig. 7}} & - \\ \hline \\ \text{reverse recovery time} & I_{_{F}} = 1 \text{ A; } V_{_{R}} = 30 \text{ V; } dI_{_{F}}/dt = 200 \text{ A/}\mu\text{s; } \\ T_{_{J}} = 25 \text{ °C; } \underline{\text{Fig. 7}} & - \\ \hline \\ I_{_{F}} = 5 \text{ A; } V_{_{R}} = 200 \text{ V; } dI_{_{F}}/dt = 200 \text{ A/}\mu\text{s; } \\ T_{_{J}} = 25 \text{ °C; } \underline{\text{Fig. 7}} & - \\ \hline \\ I_{_{F}} = 5 \text{ A; } V_{_{R}} = 200 \text{ V; } dI_{_{F}}/dt = 200 \text{ A/}\mu\text{s; } \\ T_{_{J}} = 25 \text{ °C; } \underline{\text{Fig. 7}} & - \\ \hline \\ I_{_{F}} = 5 \text{ A; } V_{_{R}} = 200 \text{ V; } dI_{_{F}}/dt = 200 \text{ A/}\mu\text{s; } \\ T_{_{J}} = 25 \text{ °C; } \underline{\text{Fig. 7}} & - \\ \hline \\ \text{peak reverse recovery current} & I_{_{F}} = 5 \text{ A; } V_{_{R}} = 200 \text{ V; } dI_{_{F}}/dt = 200 \text{ A/}\mu\text{s; } \\ T_{_{J}} = 25 \text{ °C; } \underline{\text{Fig. 7}} & - \\ \hline \\ \text{l}_{_{F}} = 5 \text{ A; } V_{_{R}} = 200 \text{ V; } dI_{_{F}}/dt = 200 \text{ A/}\mu\text{s; } \\ \hline \\ T_{_{J}} = 25 \text{ °C; } \underline{\text{Fig. 7}} & - \\ \hline \\ \text{peak reverse recovery current} & I_{_{F}} = 5 \text{ A; } V_{_{R}} = 200 \text{ V; } dI_{_{F}}/dt = 200 \text{ A/}\mu\text{s; } \\ \hline \\ T_{_{J}} = 25 \text{ °C; } \underline{\text{Fig. 7}} & - \\ \hline \\ \text{l}_{_{F}} = 5 \text{ A; } V_{_{R}} = 200 \text{ V; } dI_{_{F}}/dt = 200 \text{ A/}\mu\text{s; } \\ \hline \\ T_{_{J}} = 25 \text{ °C; } \underline{\text{Fig. 7}} & - \\ \hline \\ \text{l}_{_{F}} = 5 \text{ A; } V_{_{R}} = 200 \text{ V; } dI_{_{F}}/dt = 200 \text{ A/}\mu\text{s; } \\ \hline \\ T_{_{J}} = 25 \text{ °C; } \underline{\text{Fig. 7}} & - \\ \hline \\ \text{l}_{_{F}} = 5 \text{ A; } V_{_{R}} = 200 \text{ V; } dI_{_{F}}/dt = 200 \text{ A/}\mu\text{s; } \\ \hline \\ T_{_{J}} = 25 \text{ °C; } \underline{\text{Fig. 7}} & - \\ \hline \\ \text{l}_{_{F}} = 5 \text{ A; } V_{_{R}} = 200 \text{ V; } dI_{_{F}}/dt = 200 \text{ A/}\mu\text{s; } \\ \hline \\ T_{_{J}} = 25 \text{ °C; } \underline{\text{Fig. 7}} & - \\ \hline \\ \text{l}_{_{F}} = 5 \text{ A; } V_{_{R}} = 200 \text{ V; } dI_{_{F}}/dt = 200 \text{ A/}$	$ \begin{array}{c} \text{reacteristics} \\ \text{forward voltage} \\ & I_{\text{F}} = 5 \text{A}; T_{\text{J}} = 25 ^{\circ}\text{C}; \underline{\text{Fig. 6}} \\ & I_{\text{F}} = 5 \text{A}; T_{\text{J}} = 150 ^{\circ}\text{C}; \underline{\text{Fig. 6}} \\ & V_{\text{R}} = 600 \text{V}; T_{\text{J}} = 25 ^{\circ}\text{C} \\ & V_{\text{R}} = 600 \text{V}; T_{\text{J}} = 25 ^{\circ}\text{C} \\ & V_{\text{R}} = 600 \text{V}; T_{\text{J}} = 150 ^{\circ}\text{C} \\ \end{array} $ $ \begin{array}{c} \text{recovered charge} \\ & I_{\text{F}} = 5 \text{A}; V_{\text{R}} = 200 \text{V}; dI_{\text{F}}/dt = 200 \text{A/\mus}; \\ & T_{\text{J}} = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}} \\ & I_{\text{F}} = 5 \text{A}; V_{\text{R}} = 200 \text{V}; dI_{\text{F}}/dt = 200 \text{A/\mus}; \\ & T_{\text{J}} = 125 ^{\circ}\text{C}; \underline{\text{Fig. 7}} \\ & I_{\text{F}} = 1 \text{A}; V_{\text{R}} = 30 \text{V}; dI_{\text{F}}/dt = 200 \text{A/\mus}; \\ & T_{\text{J}} = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}} \\ & I_{\text{F}} = 5 \text{A}; V_{\text{R}} = 200 \text{V}; dI_{\text{F}}/dt = 200 \text{A/\mus}; \\ & T_{\text{J}} = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}} \\ & I_{\text{F}} = 5 \text{A}; V_{\text{R}} = 200 \text{V}; dI_{\text{F}}/dt = 200 \text{A/\mus}; \\ & T_{\text{J}} = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}} \\ & I_{\text{F}} = 5 \text{A}; V_{\text{R}} = 200 \text{V}; dI_{\text{F}}/dt = 200 \text{A/\mus}; \\ & T_{\text{J}} = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}} \\ & I_{\text{F}} = 5 \text{A}; V_{\text{R}} = 400 \text{V}; dI_{\text{F}}/dt = 200 \text{A/\mus}; \\ & T_{\text{J}} = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}} \\ & I_{\text{F}} = 5 \text{A}; V_{\text{R}} = 200 \text{V}; dI_{\text{F}}/dt = 200 \text{A/\mus}; \\ & T_{\text{J}} = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}} \\ & I_{\text{F}} = 5 \text{A}; V_{\text{R}} = 200 \text{V}; dI_{\text{F}}/dt = 200 \text{A/\mus}; \\ & T_{\text{J}} = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}} \\ & I_{\text{F}} = 5 \text{A}; V_{\text{R}} = 200 \text{V}; dI_{\text{F}}/dt = 200 \text{A/\mus}; \\ & T_{\text{J}} = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}} \\ & I_{\text{F}} = 5 \text{A}; V_{\text{R}} = 200 \text{V}; dI_{\text{F}}/dt = 200 \text{A/\mus}; \\ & T_{\text{J}} = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}} \\ & I_{\text{F}} = 5 \text{A}; V_{\text{R}} = 200 \text{V}; dI_{\text{F}}/dt = 200 \text{A/\mus}; \\ & I_{\text{F}} = 5 \text{A}; V_{\text{R}} = 200 \text{V}; dI_{\text{F}}/dt = 200 \text{A/\mus}; \\ & I_{\text{F}} = 5 \text{A}; V_{\text{R}} = 200 \text{V}; dI_{\text{F}}/dt = 200 \text{A/\mus}; \\ & I_{\text{F}} = 5 \text{A};$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$



 $V_o = 1.833 \text{ V}; R_s = 0.055 \Omega$

(1) $T_i = 150 \,^{\circ}\text{C}$; typical values

(2) T_i = 150 °C; maximum values



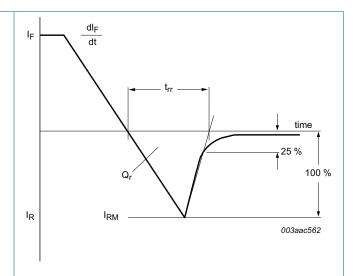
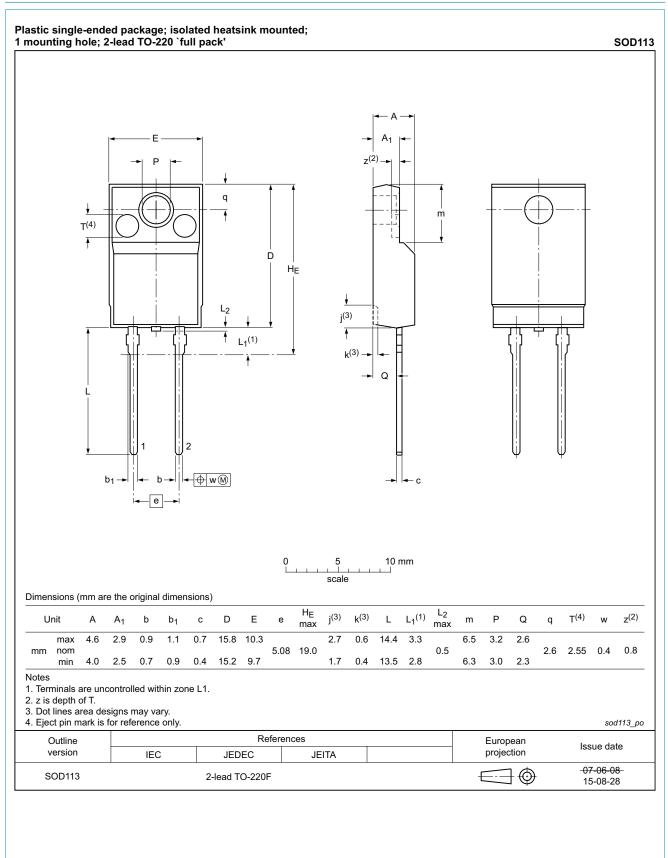


Fig. 7. Reverse recovery definitions; ramp recovery

12. Package outline



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13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [2] The term 'short data sheet' is explained in section "Definitions".
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Hyperfast power diode

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For more information, please visit: http://www.ween-semi.com For sales office addresses, please send an email to: salesaddresses@ween-semi.com Date of release: 28 April 2018

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